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Plamen Tzviatkov, FUJIFILM Electronic Materials U.S.A., Inc. (United States)
Todd R. Younkin, Intel Corporation (Belgium)

Session Chairs

1 Keynote Session
Thomas I. Wallow, ASML US, Inc. (United States)
Christoph K. Hohle, Fraunhofer Institute for Photonics Microsystems IPMS (Germany)

2 New EUV Resist Materials: Joint Session with Conferences 9048 and 9051
Robert L. Brainard, College of Nanoscale Science & Engineering, University at Albany (United States)
James W. Thackeray, Dow Electronic Materials (United States)

3 Stochastics and EUV Process Improvements: Joint Session with Conferences 9048 and 9051
Roel Gronheid, IMEC (Belgium)
Uzodinma Okoroanyanwu, GLOBALFOUNDRIES Inc. (Germany)

4 SEM Simulation and Emulation I: Joint Session with Conferences 9050 and 9051
Shunsuke Koshihara, Hitachi High-Technologies Corporation (Japan)
Thomas I. Wallow, ASML US, Inc. (United States)

5 SEM Simulation and Emulation II: Joint Session with Conferences 9050 and 9051
Benjamin D. Bunday, SEMATECH Inc. (United States)
Clifford L. Henderson, Georgia Institute of Technology (United States)

6 New Materials and Processes
Robert Allen, IBM Almaden Research Center (United States)
Ramakrishnan Ayothi, JSR Micro, Inc. (United States)

7 DSA Materials I
Ralph R. Dammel, AZ Electronic Materials USA Corporation (United States)
Douglas Guerrero, Brewer Science, Inc. (United States)

8 DSA Materials and Processes I: Joint Session with Conferences 9049 and 9051
Benjamen M. Rathsack, Tokyo Electron America, Inc. (United States)
Roel Gronheid, IMEC (Belgium)

9 DSA Materials and Processes II: Joint Session with 9049 and 9051
James A. Liddle, National Institute of Standards and Technology (United States)
Sean D. Burns, IBM Corporation (United States)

10 Materials and Process Fundamentals
Todd R. Younkin, Intel Corporation (United States)
Clifford L. Henderson, Georgia Institute of Technology (United States)

11 Advanced Patterning Processes
Plamen Tzviatkov, FUJIFILM Electronic Materials U.S.A., Inc. (United States)
Douglas Guerrero, Brewer Science, Inc. (United States)

12 DSA Materials II
Mark H. Somervell, Tokyo Electron America, Inc. (United States)
Daniel P. Sanders, IBM Almaden Research Center (United States)

13 Underlayers and Spin-on Materials Processing
Robert Allen, IBM Almaden Research Center (United States)
Christoph K. Hohle, Fraunhofer Institute for Photonic Microsystems IPMS (Germany)

14 EUV Materials
Scott W. Jessen, Texas Instruments Inc. (United States)
Thomas I. Wallow, ASML US, Inc. (United States)